

SD103AW THRU SD103CW

SMALL SIGNAL SCHOTTKY DIODES

FEATURES

- · For general purpose applications
- The SD103AW to SD103CW series is a Metal-on-silicon Schottky barrier device which is protected by a PN junction guard ring. The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing, and coupling diodes for fast switching and low logic level applications. Other applications are click suppressions, efficient full wave bridges in telephone subsets, and blocking diodes in rechargeable low voltage battery systems.
- These diodes are also available in the Mini-MELF case with the type designation LL103A thru LL103C, in the DO-35 case with type designation SD103A to SD103C and in the SOD-323 case with type designation SD103AWS to SW103CWS

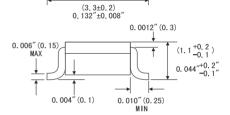
MECHANICAL DATA

· Case: SOD-123 plastic case

· Weight: Approx. 0.01 gram

0. 022"±0. 0004" (0. 55±0. 1) (1. 6 ^{+0. 2}/_{-0. 1} 0. 064"+0. 0008" 0. 108"+0. 0008" 0. 108"+0. 0008"

SOD-123



Dimensions in inches and (millimeters)

ABSOLUTE RATINGS (LIMITING VALUES)

		Symbols	Value	Units
Peak Reverse Voltage	SD103AW SD103BW SD103CW	Vrrm Vrrm Vrrm	40 30 20	V V V
Power Dissipation (infinite Heat Sink)		Ptot	400 1)	mW
Maximum Single cycle surge 60Hz sine wave		IFSM	15	Α
Junction temperature		TJ	125	ొ
Storage Temperature Range		Tstg	-55 to+150	°
1) Valid provided that el;ectrodes are kept at amb	ient temperature		_	

ELECTRICAL CHARACTERISTICS

(Ratings at 25°C ambient temperature unless otherwise specified)

		Symbols	Min.	Тур.	Max.	Unis
Leakage current at V_R =30V V_R =20V V_R =10V	SD103AW SD103BW SD103CW	lr lr lr			5 5 5	μΑ μΑ μΑ
Forward voltage drop at IF=20mA IF=200mA		VF VF			0.37 0.6	V V
Junction Capacitance at V _R =0V ,f=1M	Hz	Cı		50		pF
Reverse Recovery time at $I_F = I_R = 50 \text{mA}$, recover to 0.1 I_R	ecover to 200mA	trr		10		ns
Thermal resistance, junction to Ambient		RθJA			300 1)	K/W